

K277 SIDAC

General Description

The new K277 is a higher energy sidac switch for applications requiring higher current pulse current especially at low repetition rates. It is offered in a DO15X axial leaded package. Voltage activation of this solid state switch is accomplished with peak voltage level of 210 to 230 Volts. The sidac is a silicon bilateral voltage triggered thyristor switch that switches on through a negative resistance region to a low on-state voltage. Conduction will continue until current is interrupted or lowered below minimum holding current of the device.

The K277 sidac has a repetitive off-state blocking voltage of 190V minimum that is ensured by glass passivated junctions for best reliability. Package is epoxy encapsulation with copper alloy leads.

Features

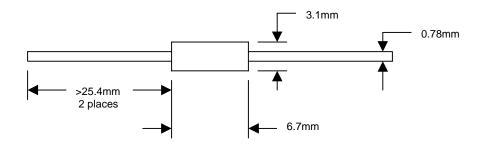
- AC circuit oriented
- DO-15X axial package
- 280A pulse current capability
- 210V to 230V triggering
- **■** RoHS Compliant

K277 Electrical Specifications

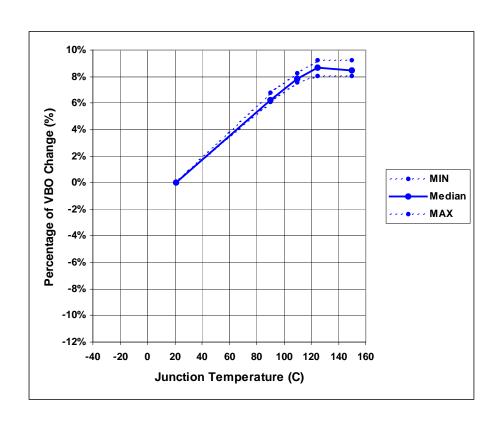
Parameters			Min	Max	Unit
V _{BO}	Breakover/Trigger Voltage	50/60Hz Sine Wave	210	230	V
V _{DRM}	Repetitive Peak Off-State Voltage		190		V
V_{TM}	Peak On-State Voltage	$I_T = 1A$		1.5	V
I _{T(RMS)}	On-State RMS Current, T _J < 125C	50/60Hz Sine Wave		1	Α
I _H	Dynamic Holding Current, R=100 Ω	50/60Hz Sine Wave		80	mA
Rs	Switching Resistance, $R_S = \frac{(V_{BO} - V_S)}{(I_S - I_{BO})}$	50/60Hz Sine Wave		100	Ω
I _{BO}	Breakover Current	50/60Hz Sine Wave		100	uA
I _{TRM}	Pulse On-State Current, width 10usec Pulse On-State Current, width 10usec	60Hz 5Hz		120 280	A A
di/dt	Critical Rate of Rise of On-State Current			150	A/usec
dv/dt	Critical Rate of Rise of Off-State Voltage			1500	V/usec
Ts	Storage Temperature Range		-40	+150	°C
TJ	Max Operating Junction Temperature			+150	°C
R _{0J L}	Thermal Resistance	Junction to lead		18	°C/W



DO-15X Outline Dimensions



V_{BO} Derating by Operating Temperature



I_{TRM} Derating by Frequency and Pulse Width

